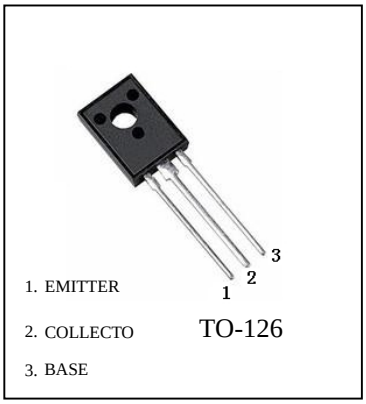
B772 (PNP)

FEATURES

Low speed switching

MARKING:772



MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current -Continuous	I_C	-3000	mA
Collector Power Dissipation	P_C	1250	mW
Junction Temperature	T_J	150	℃
Storage Temperature	Tstg	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25 ℃ unless otherwise specified)

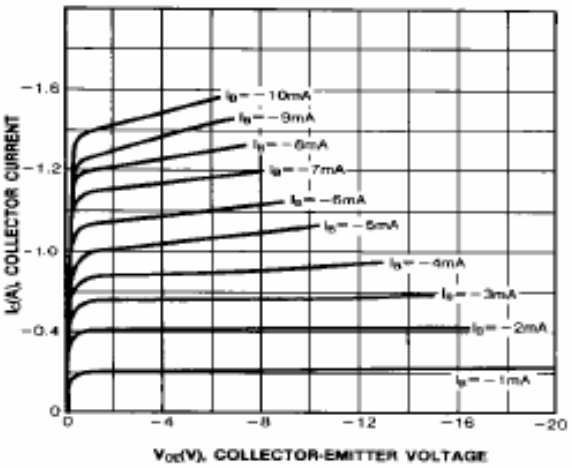
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	VCBO	IC=-100μA ,IE=0	-40			V
Collector-emitter breakdown voltage	VCEO	IC= -10mA , IB=0	-30			V
Emitter-base breakdown voltage	VEBO	IE= -100μA,IC=0	-5			V
Collector cut-off current	ICBO	VCB= -40V, IE=0			-1	μA
Collector cut-off current	ICEO	VCE=-30V, IB=0			-10	μA
Emitter cut-off current	IEBO	VEB=-6V, IC=0			-1	μA
DC current gain	hFE	VCE= -2V, IC= -1A	60		400	
Collector-emitter saturation voltage	VCE(sat)	IC=-2A, IB= -0.2A			-0.5	V
Base-emitter saturation voltage	VBE(sat)	IC=-2A, IB= -0.2A			-1.5	V
Transition frequency	fT	VCE= -5V, IC=-0.1A,f =10MHz		80		MHz

CLASSIFICATION OF HFE

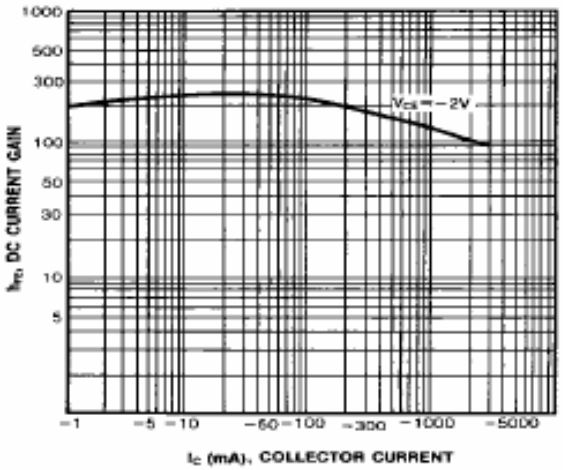
Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

B772 Typical Characteristics

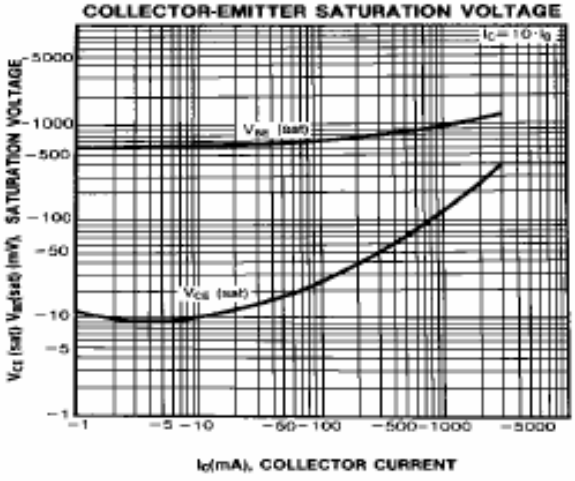
STATIC CHARACTERISTIC



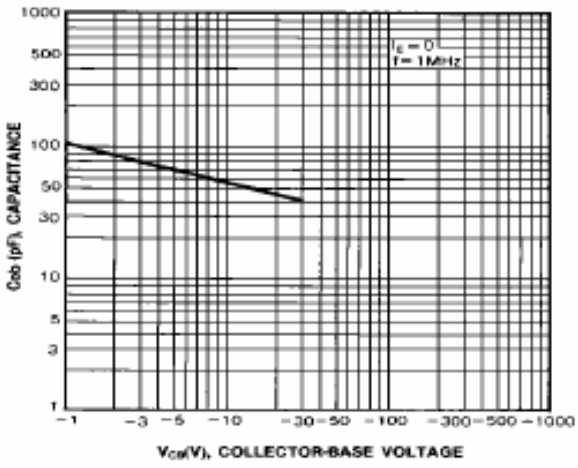
DC CURRENT GAIN



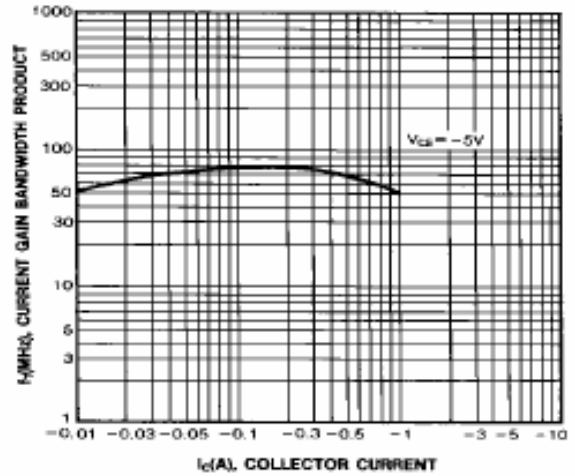
BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



CURRENT GAIN-BANDWIDTH PRODUCT



SAFE OPERATING AREA